查询"2SK3312"(共享回答 Field Effect Transistor Silicon N Channel MOS Type (π--MOSV)

2SK3312

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & \vdots\ RDS\ (ON) = 0.9\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & \vdots\ |\ Y_{fs}\ | = 3.5\ S\ (typ.) \\ \bullet & Low\ leakage\ current & \vdots\ IDSS = 100\ \mu A\ (max)\ (V_{DS} = 600\ V) \\ \bullet & Enhancement\ mode & \vdots\ V_{th} = 3.0 \sim 5.0\ V\ (V_{DS} = 10\ V,\ I_{D} = 1\ mA) \\ \end{array}$

Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V_{DGR}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	6	Α	
	Pulse (Note 1)	I_{DP}	24	Α	
Drain power dissipatio	n (Tc = 25°C)	P_{D}	65	W	
Single pulse avalanche	e energy (Note 2)	E _{AS}	345	mJ	
Avalanche current		I _{AR}	6	Α	
Repetitive avalanche	energy (Note 3)	E _{AR}	6.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature r	ange	T _{stg}	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.92	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

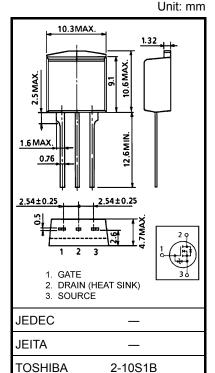
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 16.8 mH, R_G = 25 Ω , I_{AR} = 6 A

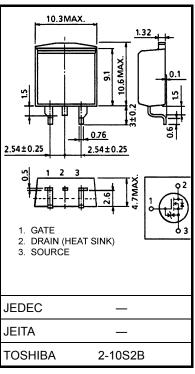
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



Weight: 1.5 g (typ.)



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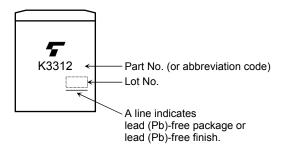
Energy istics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold v	voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	_	5.0	V
Drain-source O	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 3 A	_	0.9	1.25	Ω
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	1.2	3.5	_	S
Input capacitano	e	C _{iss}		_	1000	_	
Reverse transfe	Reverse transfer capacitance C_{rss} $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		_	8	_	pF	
Output capacitance		Coss]		110		_
Switching time	Rise time	t _r	V_{GS} V_{OUT} V_{OUT} V_{DD} V_{OUT} V_{DD}	_	15	_	
	Turn-on time	t _{on}		_	30	_	no
	Fall time	t _f		_	10	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$	_	55	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	21	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$		12	_	nC
Gate-drain ("miller") Charge		Q_{gd}			9	_	

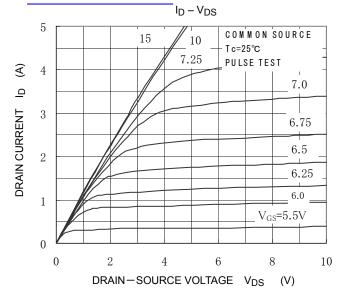
Source-Drain Ratings and Characteristics (Ta = 25°C)

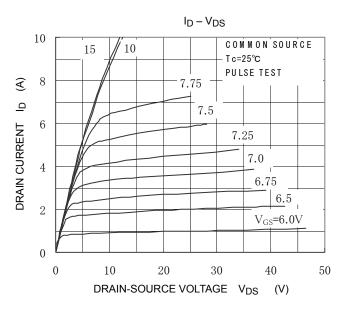
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	6	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	24	Α
Forward voltage (diode)	V_{DSF}	I _{DR} = 6 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V}, dI_{DR} / dt = 100 \text{ A} / \mu \text{s}$		1000	_	ns
Reverse recovery charge	Q _{rr}		_	7	_	μC

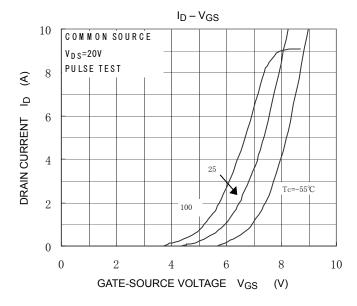
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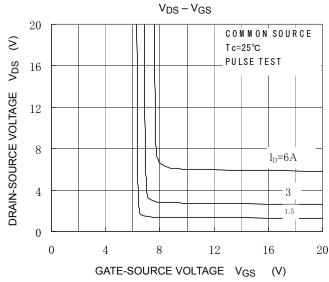


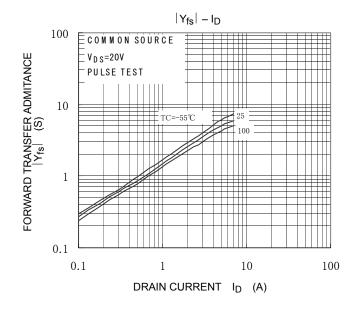
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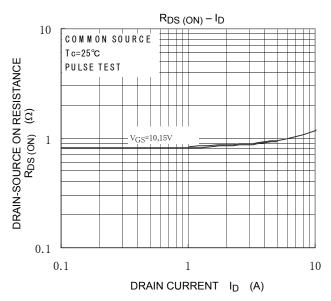






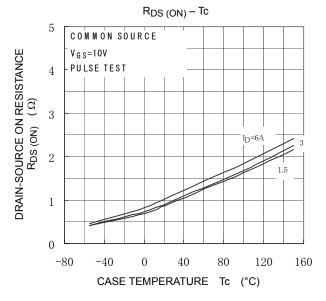


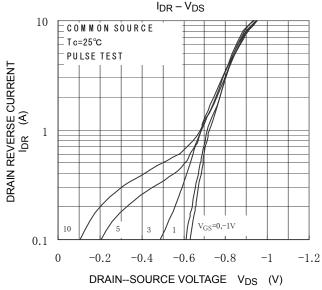


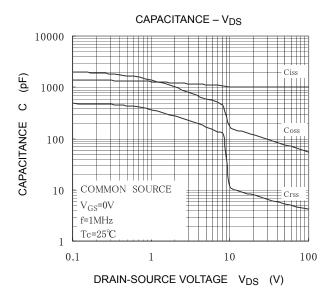


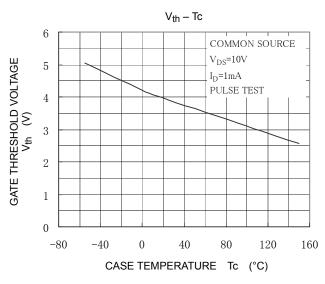
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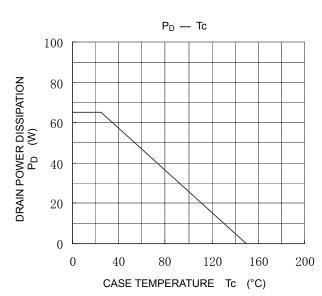
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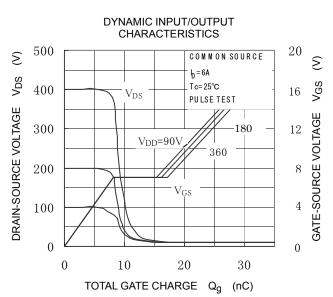




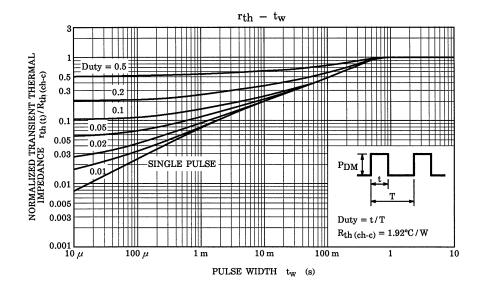


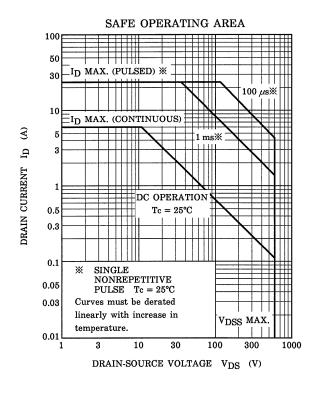


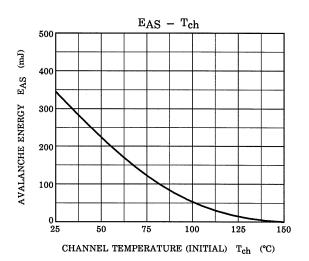


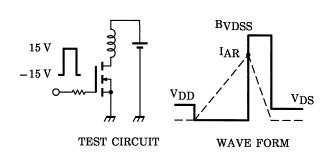


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$$R_G = 25 \Omega$$

 $V_{DD} = 90 \text{ V, L} = 16.8 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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